

ELENCO DELLE PUBBLICAZIONI E DEI LAVORI A STAMPA RAGGRUPPATI IN MODO ANALITICO DI ANDREA CANDELORI. IN NUMERO TOTALE DI 99 (98 PUBBLICAZIONI E LA TESI DI DOTTORATO).

A) SPICE SIMULATION OF SILICON DETECTORS

PA1) "A Network Analysis of Signal Propagation in Si Microstrip Detectors", N. Bacchetta, D. Bisello, A. Candelori, A. Paccagnella, M. Spada and M. Vanzi, IEEE Nuclear Science Symposium and Medical Imaging Conference Record, 1994, pp.679-683.

PA2) "A SPICE Model of Si Microstrip Detectors", N. Bacchetta, D. Bisello, C. Calgarotto, A. Candelori and A. Paccagnella, IEEE Nuclear Science Symposium and Medical Imaging Conference Record, 1995, pp.510-514.

PA3) "A SPICE Model of Double-sided Si Microstrip Detectors", A. Candelori, A. Paccagnella, F. Bonin, N. Bacchetta, M. Da Rold and D. Bisello, IEEE Nuclear Science Symposium and Medical Imaging Conference Record, 1996, pp.568-572.

PA4) "SPICE Analysis of Signal Propagation in Si Microstrip Detectors", N. Bacchetta, D. Bisello, A. Candelori, A. Paccagnella, M. Spada and M. Vanzi, IEEE Transactions on Nuclear Science vol.42, n.4, August 1995, pp.459-466.

PA5) "A SPICE Model for Si Microstrip Detectors and Read-out Electronics", N. Bacchetta, D. Bisello, C. Calgarotto, A. Candelori and A. Paccagnella, IEEE Transactions on Nuclear Science, vol.43, n.3, June 1996, pp.1213-1219.

PA6) "A SPICE Model of the Ohmic Side of Double-Sided Si Microstrip Detectors", A. Candelori, A. Paccagnella, F. Bonin, N. Bacchetta, M. Da Rold and D. Bisello, IEEE Transactions on Nuclear Science, vol.44, n.3, June 1997, pp. 728-735.

PA7) "HSPICE Simulations of Si Microstrip Detectors", N. Bacchetta, D. Bisello, A. Candelori, M. Da Rold, F. Nardi and A. Paccagnella, Nuclear Instruments and Methods in Physics Research, vol.A409, 1998, pp.142-146.

PA8) "SPICE Evaluation of the S/N Ratio for Si Microstrip Detectors", A. Candelori, A. Paccagnella, F. Nardi, N. Bacchetta and D. Bisello, Il Nuovo Cimento, vol.112A, Gennaio-Febbraio 1999, pp.75-85.

PA9) "SPICE Evaluation of the S/N Ratio for Si Microstrip Detectors", A. Candelori, A. Paccagnella, F. Nardi, N. Bacchetta and D. Bisello, IEEE Transactions on Nuclear Science, vol.46, n.5, October 1997, pp.1261-1273.

B) RADIATION EFFECTS IN CMOS AND JFET TECHNOLOGIES

PB1) "Breakdown Properties of Irradiated MOS Capacitors", A. Paccagnella, A. Candelori, A. Milani, E. Formigoni, G. Ghidini, F. Pellizzer, D. Drera, P. G. Fuochi and M. Lavale, IEEE Transactions on Nuclear Science, vol.43, n.6, December 1996, pp.2609-2616.

PB2) "Modifications of Fowler-Nordheim injection characteristics in γ irradiated MOS devices", A. Scarpa, A. Paccagnella, F. Montera, A. Candelori, G. Ghibauda, G. Pananakakis, G. Ghidini, P. G. Fuochi, Proceedings of the 4th European Conference on Radiation and Its Effects on Components and Systems (RADECS), 15-19 September 1997, pp.73-78.

PB3) "Modification of Fowler-Nordheim Injection Characteristics in γ Irradiated MOS Devices", A. Scarpa, A. Paccagnella, F. Montera, A. Candelori, G. Ghibauda, G. Pananakakis, G. Ghidini and P. G. Fuochi, IEEE Transactions on Nuclear Science, vol.45, n.3, June 1998, pp.1390-1395.

PB4) "Fowler-Nordheim Characteristics of Electron Irradiated MOS Capacitors", A. Candelori, A. Paccagnella, M. Cammarata, G. Ghidini, P. G. Fuochi, IEEE Transactions on Nuclear Science, vol.45, n.6, December 1998, pp.2383-2390.

PB5) "MOSFET Parameter Degradation after Folwer-Nordheim Injection Stress", A. Candelori, G. Gomiero, G. Ghidini and A. Paccagnella, Microelectronics Reliability, vol.38, n.2, 1998, pp.189-193.

PB6) "Degradation of Electron Irradiated MOS capacitors", A. Candelori, A. Paccagnella, A. Scarpa, G. Ghidini and P. G. Fuochi, Microelectronics Reliability, vol.39, 1999, pp.227-233.

PB7) "Electron Irradiation Effects on thin MOS Capacitors", A. Candelori, A. Paccagnella, M. Cammarata, G. Ghidini and M. Ceschia, Journal of Non-Crystalline Solids, vol.245, 1999, pp.238-244.

PB8) "Low-field Current on Thin Oxides After Constant Current or Radiation Stresses", M. Ceschia, A. Paccagnella, A. Cester, A. Scarpa, A. Candelori and G. Ghidini, Journal of Non-Crystalline Solids, vol.245, 1999, pp.232-237.

PB9) "Breakdown of Coupling Dielectrics for Si Microstrip Detectors", A. Candelori, A. Paccagnella, G. Saglimbeni and D. Bisello, *Il Nuovo Cimento*, vol.112A, Gennaio-Febbraio 1999, pp.87-93.

PB10) "Heavy Ion Irradiation of Thin Gate Oxides", M. Cerchia, A. Paccagnella, M. Turrini, A. Candelori, G. Ghidini and J. Wyss, *IEEE Transactions on Nuclear Science*, vol.47, n.6, December 2000, pp.2648-2655.

PB11) "High Energy Si Ion Irradiation Effects on 10 nm Thick Oxide MOS Capacitors", A. Candelori, A. Paccagnella, G. Raggi, J. Wyss, D. Bisello and G. Ghidini, *Journal of Non-Crystalline Solids*, vol.280, 2001, pp.193-201.

PB12) "Thin Oxide Degradation After High-Energy Ion Irradiation", A. Candelori, M. Ceschia, A. Paccagnella, J. Wyss, D. Bisello and G. Ghidini, *IEEE Transactions on Nuclear Science*, vol.48, n.5, October 2001, pp.1735-1743.

PB13) "High-Energy Ion Irradiation Effects on Thin Oxide p-Channel MOSFETs", A. Candelori, D. Contarato, N. Bacchetta, D. Bisello, G. Hall, E. Noah, M. Raymond and J. Wyss, *IEEE Transactions on Nuclear Science*, vol.49, n.3, June 2002, pp.1364-1370.

PB14) "Comparison of Ionizing Radiation Effects in 0.18 and 0.25 μm CMOS Technologies for Analog Applications", M. Maghisoni, L. Ratti, V. Re, V. Speziali, G. Traversi and A. Candelori, *IEEE Transactions on Nuclear Science*, vol.50, n.6, December 2003, pp.1827-1833.

PB15) "Statistical Model for Radiation-Induced Wear-Out of Ultra-Thin Gate Oxides After Exposure to Heavy Ion Irradiation", A. Cester, S. Cimino, E. Miranda, A. Candelori, G. Ghidini and A. Paccagnella, *IEEE Transactions on Nuclear Science*, vol.50, n.6, December 2003, pp.2167-2175.

PB16) "Drain Current Decrease in MOSFETs After Heavy Ion Irradiation", A. Cester, S. Gerardin, A. Paccagnella, J. R. Schwank, G. Vizkelethy, A. Candelori and G. Ghidini, *IEEE Transactions on Nuclear Science*, vol.51, n.6, December 2004, pp.3150-3157.

PB17) "Impact of 24-GeV proton irradiation on 0.13- μ m CMOS devices", S. Gerardin, A. Gasperin, A. Cester, A. Paccagnella, G. Ghidini, A. Candelori, N. Bacchetta, D. Bisello, M. Glaser, IEEE Transactions on Nuclear Science, vol.53, n.4, August 2006, pp.1917-1922.

PB18) "Radiation Damage Studies of Detector-compatible Si JFETs", G. F. Dalla Betta, M. Boscardin, A. Candelori, L. Pancheria., C. Piemonte, L. Ratti, N. Zorzi, Nuclear Instruments and Methods in Physics Research, vol.A572, 2007, pp.287–289.

PB19) "Proton Induced Damage in JFET Transistors and Charge Preamplifiers on High-Resistivity Silicon", G.-F. Dalla Betta, M. Manghisoni, L. Ratti, V. Re, V. Speziali, G. Traversi and A. Candelori, Proceedings of the 7th European Conference on Radiation and Its Effects on Components and Systems (RADECS), 15-19 September 2003, ESA SP-536, pp.419-424.

PB20) "Proton Induced Damage in JFET Transistors and Charge Preamplifiers on High-Resistivity Silicon", G.-F. Dalla Betta, M. Manghisoni, L. Ratti, V. Re, V. Speziali, G. Traversi and A. Candelori, IEEE Transactions on Nuclear Science, vol.51, n.5, October 2004, pp.2880-2866.

C) RADIATION EFFECTS IN SILICON DETECTORS

PC1) "Radiation Induced Bulk Damage in Silicon Diodes with Pions and Protons", N. Bacchetta, D. Bisello, A. Candelori, A. Giraldo, M. Loreti, D. Pantano and A. Pellizzari, Nuclear Instruments and Methods in Physics Research, vol.A338, 1997, pp.318-322.

PC2) "Observation of an Energy Dependence of the Radiation Damage on Standard and Oxygenated Silicon Diodes by 16, 21 and 27 MeV Protons", J. Wyss, D. Bisello, A. Candelori, A. Kaminski and D. Pantano, Nuclear Instruments and Methods in Physics Research, vol.A457, 2001, pp.595-600.

PC3) "Radiation Effects on Standard and Oxygenated Silicon Diodes", D. Bisello, A. Candelori, A. Kaminski, D. Pantano, R. Rando, J. Wyss, A. Andrighetto, V. Cindro, Proceedings of the Nuclear Science Symposium (NSS), 4-10 November 2001, pp.189-196.

PC4) "Radiation Damage of Standard and Oxygenated Silicon Diodes Irradiated by 16-MeV and 27-MeV Protons", A. Candelori, R. Rando, D. Bisello, N. Bacchetta, A. Kaminski, D. Pantano, I. Stavitski and J. Wyss, IEEE Transactions on Nuclear Science, vol.48, n.4, August 2001, pp.1020-1027.

PC5) "Low- and High-Energy Proton Irradiations of Standard and Oxygenated Silicon Diodes", D. Bisello, J. Wyss, A. Candelori, A. Kaminski and D. Pantano, IEEE Transactions on Nuclear Science, vol.48, n.6, December 2001, pp.2270-2277.

PC6) "Neutron Irradiation Effects on Standard and Oxygenated Silicon Diodes", D. Bisello, A. Candelori, A. Kaminski, D. Pantano, R. rando, J. Wyss, A. Andrighetto and V. Cindro, IEEE Transactions on Nuclear Science, vol.49, n.3, June 2002, pp.1027-1034.

PC7) "Charge Collection Efficiency of Standard and Oxygenated Silicon Microstrip Detectors", I. Stavitski, R. Rando, D. Bisello, N. Bacchetta, A. Candelori, A. Kaminski and J. Wyss, Nuclear Instruments and Methods in Physics Research, vol.A485, 2002, pp.105-108.

PC8) "Radiation Hardness of Silicon Detectors for High-Energy Physics Applications", A. Candelori, D. Bisello, R. Rando, A. Kaminski, J. Wyss, A. Litovchenko, G.-F. Dalla Betta, M.

Lozano, M. Boscardin, C. Martinez, M. Ullan and N. Zorzi, IEEE Transactions on Nuclear Science, vol.50, n.4, August 2003, pp.1121-1128.

PC9) "New Evidence of Dominant Processing Effects in Standard and Oxygenated Silicon Diodes After Neutron Irradiation ", A. Candelori, R. Rando, D. Bisello, A. Kaminski, F. Campabadal, V. Cindro, L. Fonseca, A. Kaminski, A. Litovchenko, M. Lozano, C. Martinez, A. Moreno, J. M. Rafi, J. Santader, M. Ullán and J. Wyss, Nuclear Instruments and Methods in Physics Research, vol.A521, 2003, pp.52-59.

PC10) "Silicon Diode Radiation Hardening for High Energy Physics Detectors", R. Rando, A. Candelori, D. Bisello, A. Kaminski, A. Litovchenko, D. Pantano, I. Stavitski and J. Wyss, Nuclear Instruments and Methods in Physics Research, vol.A514, 2003, pp.62-68.

PC11) "Lithium Ion Irradiation of Standard and Oxygenated Silicon Diodes", A. Candelori, D. Bisello, G.-F. Dalla Betta, P. Giubilato, A. Kaminski, A. Litovchenko, M. Lozano, J. R. Petrie, R. Rando, M. Ullán and J. Wyss, Proceedings of the 7th European Conference on Radiation and Its Effects on Components and Systems (RADECS), 15-19 September 2003, ESA SP-536, pp.393-399.

PC12) "Lithium Ion-Induced Damage in Silicon Detectors", A. Candelori, D. Bisello, P.Giubilato, A. Kaminski, A. Litovchenko, M. Lozano, M. Ullán, R. Rando and J. Wyss, Nuclear Instruments and Methods in Physics Research, vol.A518, 2004, pp.338-339.

PC13) "Lithium Ion Irradiation Effects on Epitaxial Silicon Detectors", A. Candelori, A. Schramm, D. Bisello, D. Contarato, E. Fretwurst, G. Lindstrom, R. Rando and J. Wyss, IEEE Transactions on Nuclear Science, vol.51, n.4, August 2004, pp.1766-1772.

PC14) "Lithium Ion Irradiation of Standard and Oxygenated Silicon Diodes", A. Candelori, D. Bisello, G.-F. Dalla Betta, P. Giubilato, A. Kaminski, A. Litovchenko, M. Lozano, J. R. Petrie, R. Rando, M. Ullán and J. Wyss, IEEE Transactions on Nuclear Science, vol.51, n.5, October 2004, pp.2865-2871.

PC15) "Radiation Hardness of Semiconductor Detectors for High Energy Physics Applications", D. Bisello, A. Candelori, P. Giubilato, A. Kaminski, A. Litovchenko, D. Pantano, R. Rando and J. Wyss, Radiation Physics and Chemistry, vol.71, 2004, pp.709-711.

PC16) "Radiation Hardness and Charge Collection Efficiency of Lithium Irradiated Thin Silicon Diodes", M. Boscardin, M. Bruzzi, A. Candelori, G.-F. Dalla Betta, E. Focardi, V. Khomenkhov, C. Piemonte, S. Ronchin, C. Tosi and N. Zorzi, IEEE Transactions on Nuclear Science, vol.52, n.4, August 2005, pp.1048-1053.

PC17) "Semiconductor Materials and Detectors for Future Very High Luminosity Colliders", A. Candelori, IEEE Transactions on Nuclear Science, vol.52, n.6, December 2005, pp.2554-2561.

PC18) "Radiation-hard Semiconductor Detectors for SuperLHC", M. Bruzzi, J. Adey, ..., A. Candelori, ..., V. Zhukovff, N. Zorzi, Nuclear Instruments and Methods in Physics Research, vol.A541, 2005, pp.189-201.

PC19) "Development of Radiation Tolerant Semiconductor Detectors for the Super-LHC", M. Moll, J. Adey, ..., A. Candelori, ..., V. Zhukovag, N. Zorzi, Nuclear Instruments and Methods in Physics Research, vol.A546, 2005, pp.99-107.

PC20) "Recent Advancements in the Development of Radiation Hard Semiconductor Detectors for S-LHC", E. Fretwurst, J. Adey, ... , A. Candelori, ... , V. Zhukovag, N. Zorzi, Nuclear Instruments and Methods in Physics Research, vol.A552, 2005, pp.7-19.

PC21) "Processing and First Characterization of Detectors Made with High Resistivity n- and p-Type Czochralski Silicon", M. Bruzzi, D. Bisello, ... , A. Candelori, ... , C. Tosia, N. Zorzi, Nuclear Instruments and Methods in Physics Research, vol.A552, 2005, pp.20-26.

PC22) "Radiation-hard Detectors for Very High Luminosity Colliders", A. Candelori, Nuclear Instruments and Methods in Physics Research, vol.A560, 2006, pp.103-107.

PC23) " Irradiation Effects on Thin Epitaxial Silicon Detectors", V. Khomenkova, D. Bisello, M. Bruzzi, A. Candelori, A. Litovchenko, C. Piemonte, R. Rando, F. Ravotti, N. Zorzi, Nuclear Instruments and Methods in Physics Research, vol.A568, 2006, pp.61-65.

PC24) "Localized Energy Levels Generated in Magnetic Czochralski Silicon by Proton Irradiation and Their Influence on the Sign of Space Charge Density", M. Scaringella, D. Menichelli, ... , A. Candelori, ... , E. Verbitskayae, I. Pintilie, Nuclear Instruments and Methods in Physics Research, vol.A570, 2007, pp.322-329.

D) SILICON DETECTOR MULTI-GUARDRING STRUCTURES

PD1) "Radiation Effects on Breakdown Characteristics of Multiguarded Devices", M. Da Rold, A. Paccagnella, A. Da Re, G. Verzellesi, N. Bacchetta, R. Wheadon, G.-F. Dalla Betta, A. Candelori, G. Soncini and D. Bisello, IEEE Transactions on Nuclear Science, vol.44, n.3, June 1997, pp.721-727.

PD2) "High Voltage Operation of Silicon Devices for LHC Experiments", N. Bacchetta, D. Bisello, A. Candelori, M. Cavone, G.-F. Dalla Betta, M. Da Rold, G. De Liso, R. Dell'Orso, P. G. Fuochi, A. Messineo, A. Mihul, O. Militaru, A. Paccagnella, G. Tonelli, P. G. Verdini, G. Verzellesi and R. Wheadon, Nuclear Instruments and Methods in Physics Research, vol.A409, 1998, pp.139-141.

PD3) "High Voltage Breakdown Studies on Si Microstrip Detectors", S. Albergo, ..., A. Candelori, ..., B. Wittmer, Il Nuovo Cimento, vol.112A, n.11, Novembre 1999, pp.1271-1283.

PD4) "Improvement in Breakdown Characteristics with Multiguard Structures in Microstrip Silicon Detectors for CMS", N. Bacchetta, D. Bisello, A. Candelori, M. Da Rold, M. Descovich, A. Kaminski, A. Messineo, F. Rizzo and G. Verzellesi, Nuclear Instruments and Methods in Physics Research, vol.A461, 2001, pp.204-206.

PD5) "An Improved Termination Structure for Silicon Radiation Detectors with All-P-Type Multiguard and Cut-Line Implants", M. Boscardin, L. Bosisio, A. Candelori, G.-F. Dalla Betta, S. Dittongo, P. Gregori, C. Piemonte, I. Rachevskaia, S. Ronchin and N. Zorzi, IEEE Transactions on Nuclear Science, vol.50, n.4, August 2003, pp.1001-1007.

PD6) "Investigation of the Radiation Tolerance of All-P-Type Termination Structures for Silicon Detectors", C. Piemonte, M. Boscardin, L. Bosisio, A. Candelori, M. Ciacchi, G.-F. Dalla Betta, S. Dittongo, I. Rachevskaia and N. Zorzi, IEEE Transactions on Nuclear Science, vol.51, n.4, August 2004, pp.1747-1751.

E) CMS SILICON TRACKER

PE1) "The CMS Silicon Tracker at LHC", G. M. Bilei, ..., [A. Candelori](#), ..., B. Wittmer, Nuclear Instruments and Methods in Physics Research, vol.A409, 1998, pp.105-111.

PE2) "The CMS Silicon Tracker", R. D'Alessandro, ..., [A. Candelori](#), ..., B. Wittmer, Nuclear Instruments and Methods in Physics Research, vol.A419, 1998, pp.538-543.

PE3) "Test Results on Heavily Irradiated Silicon Detectors for the CMS Experiment at LHC", C. Bozzi, ..., [A. Candelori](#), ..., B. Wittmer, Nuclear Science Symposium Conference Record, 1998, vol.2, pp.857-862.

PE4) "Test Results of Heavily Irradiated Si Detectors", S. Albergo, ..., [A. Candelori](#), ..., B. Wittmer, Nuclear Instruments and Methods in Physics Research, vol.A422, 1999, pp.238-241.

PE5) "The CMS Silicon Microstrip Detectors: Research and Development", E. Focardi, ..., [A. Candelori](#), ..., B. Wittmer, Nuclear Instruments and Methods in Physics Research, vol.A435, 1999, pp.102-108.

PE6) "The CMS Silicon Strip Tracker", N. Bacchetta, ..., [A. Candelori](#), ..., B. Wittmer, Nuclear Instruments and Methods in Physics Research, vol.A426, 1999, pp.16-23.

PE7) "The R&D Program for Silicon Detectors in CMS", G. Tonelli, ..., [A. Candelori](#), ..., B. Wittmer, Nuclear Instruments and Methods in Physics Research, vol.A435, 1999, pp.109-117.

PE8) "Comparative Study of $\langle 111 \rangle$ and $\langle 100 \rangle$ Crystals and Capacitance Measurements on Si Strip Detectors in CMS", S. Albergo, ..., [A. Candelori](#), ..., B. Wittmer, Il Nuovo Cimento, vol.112A, n.11, Novembre 1999, pp.1261-1269.

PE9) "The Silicon Microstrip Tracker for CMS", S. Albergo, ..., [A. Candelori](#), ..., B. Wittmer, Il Nuovo Cimento, vol.112A, n.11, Novembre 1999, pp.1307-1316.

PE10) "The Silicon Microstrip Tracker for CMS", D. Pandoulas, ..., [A. Candelori](#), ..., Z. Xie, Nuclear Physics B (Proc. Suppl.), vol.78, 1999, pp.315-321.

PE11) "R&D for CMS Silicon Tracker", D. Pandoulas, ..., A. Candelori, ..., Z. Xie, Nuclear Physics B (Proc. Suppl.), vol.78, 1999, pp.322-328.

PE12) "Performance of CMS Silicon Microstrip Detector with the APV6 Readout Chip", M. Meschini, ..., A. Candelori, ..., B. Wittmer, Nuclear Instruments and Methods in Physics Research, vol.A447, 2000, pp.133-141.

PE13) "New Results on Silicon Microstrip Detectors of CMS Tracker", N. Demaria, ..., A. Candelori, ..., B. Wittmer, Nuclear Instruments and Methods in Physics Research, vol.A447, 2000, pp.142-150.

PE14) "The CMS Silicon Tracker", E. Focardi, ..., A. Candelori, ..., B. Wittmer, Nuclear Instruments and Methods in Physics Research, vol.A453, 2000, pp.121-125.

PE15) "Optimization of the Silicon Sensors for the CMS Tracker", S. Albergo, ..., A. Candelori, ..., B. Wittmer, Nuclear Instruments and Methods in Physics Research, vol.A466, 2000, pp.300-307.

PE16) "CMS Silicon Tracker Developments", C. Civinini, ..., A. Candelori, ..., B. Wittmer, Nuclear Instruments and Methods in Physics Research, vol.A477, 2000, pp.440-445.

PE17) "Test Results on Heavily Irradiated Silicon Detectors for the CMS Experiments at LHC ", C. Bozzi, ..., A. Candelori, ..., B. Wittmer, IEEE Transactions on Nuclear Science, vol.47, n.6, December 2000, pp.2092-2100.

PE18) "The CMS experiment at the CERN LHC", W. Adam, ... , A. Candelori, ..., K. V. Tsang, Journal of Instrumentations, vol.3, July 2008, P07006.

F) SIGLE EVENT EFFECT (SEE) STUDIES

FA) SEE IN ASIC

PFA1) "Radiation Testing of GLAST LAT Tracker ASICs", R. Rando, A. Bangert, D. Bisello, A. Candelori, P. Giubilato, M. Hirayama, R. Johnson, H. F.-W. Sadrozinski, M. Sugizaki, J. Wyss and M. Ziegler, IEEE Transactions on Nuclear Science, vol.51, n.3, June 2004, pp.1067-1073.

PFA2) "Radiation-Induced Effects on the XAA1.2 ASIC Chip for Space Applications", E. Del Monte, L. Pacciani, G. Porrovecchio, P. Soffitta, E. Costa, G. Di Persio, M. Feroci, M. Mastropiero, E. Morelli, M. Rapisarda, A. Rubini, D. Bisello, A. Candelori, A. Kaminski and J. Wyss, Nuclear Instruments and Methods in Physics Research, vol.A538, 2005, pp.465-482.

PFA3) "Latest Results of SEE Measurements Obtained by the Strured demonstrator ASIC ", A. Candelori, G. De Robertis, A. Gabrielli, S. Mattiazzo, D. Pantano, A. Ranieri, M. Tessaro, Nuclear Instruments and Methods in Physics Research, vol.A626-627, 2011, pp.82-89.

FB) SEE IN POWER MOSFET

PFB1) "Experimental Study of Charge Generation Mechanisms in Power MOSFETs due to Energetic Particle Impact", F. Velardi, F. Iannuzzo, G. Busatto, J. Wyss and A. Candelori, Microelectronics Reliability vol.43, 2003, pp.549-555.

PFB2) "Effect of the Epitaxial Layer Features on the Reliability of Medium Blocking Voltage Power VDMOSFET During Heavy Ion Exposure", F. Velardi, F. Iannuzzo, G. Busatto, J. Wyss, A. Sanseverino, A. Candelori, G. Currò, A. Cascio, F. Frisina, A. Cavagnoli, Proceedings of the 7th European Conference on Radiation and Its Effects on Components and Systems (RADECS), 15-19 September 2003, ESA SP-536, pp.321-325.

FC) SEE IN FPGA

PFC1) "Identification and Classification of Single-Event Upsets in the Configuration Memory of SRAM-Based FPGAs", M. Ceschia, M. Violante, M. Sonza Reorda, A. Paccagnella, P. Bernardi, M. Rebaudengo, D. Bortolato, M. Bellato, P. Zambolin and A. Candelori, IEEE Transactions on Nuclear Science, vol.50, n.6, December 2003, pp.2088-2094.

PFC2) "Analyzing SEU effects in SRAM-based FPGAs", M. Violante, M. Ceschia, M. Sonza Reorda, A. Paccagnella, P. Bernardi, M. Rebaudengo, D. Bortolato, M. Bellato, P. Zambolin and A. Candelori, Proceedings of the International On-Line Testing Symposium (IOLTS), 2003, pp. 119-123.

PFC3) "Evaluating the Effects of SEUs Affecting the Configuration Memory of an SRAM-Based FPGA", M. Bellato, P. Bernardi, D. Bortolato, A. Candelori, M. Ceschia, A. Paccagnella, M. Rebaudengo, M. Sonza Reorda, M. Violante and P. Zambolin, Proceedings of the Design, Automation and Test in Europe Conference and Exhibition (DATECE), 16-20 February 2004, pp.584-589.

FD) SEE IN FLOATING GATE MEMORIES

PFD1) "Anomalous Charge Loss from Floating-Gate Memory Cells due to Heavy Ion Irradiations", G. Cellere, A. Paccagnella, L. Larcher, A. Chimenton, J. Wyss, A. Candelori and A. Modelli, IEEE Transactions on Nuclear Science, vol.49, n.6, December 2002, pp.3051-3058.

PFD2) "Data Retention After Heavy Ion Exposure of Floating Gate Memories: Analysis and Simulations", L. Larcher, G. Cellere, A. Paccagnella, A. Chimenton, A. Candelori and A. Modelli, IEEE Transactions on Nuclear Science, vol.50, n.6, December 2003, pp.2176-2183.

PFD3) "Transient Conductive Path Induced by a Single Ion in 10 nm SiO₂ Layers", G. Cellere, A. Paccagnella, A. Visconti, M. Bonanomi and A. Candelori, IEEE Transactions on Nuclear Science, vol.51, n.6, December 2004, pp.3304-3311.

PFD4) "Effect of Different Total Ionizing Dose Sources on Charge Loss From Programmed Floating Gate Cells", G. Cellere, A. Paccagnella, A. Visconti, M. Bonanomi A. Candelori and S. Lora IEEE Transactions on Nuclear Science, vol.52, n.6, December 2005, pp.2372-2377.

G) IRRADIATION FACILITIES

PG1) "Status of the Ion Electron Emission Microscope at the SIRAD Single Event Effect Facility", D. Bisello, A. Candelori, M. Dal Maschio, P. Giubilato, A. Kaminski, M. Nigro, D. Pantano, R. Rando, S. Sedykh, M. Tessaro and J. Wyss, Nuclear Instruments and Methods in Physics Research, vol.B210, 2003, pp.142-146.

PG2) "The SIRAD Irradiation Facility for Bulk Damage and Single Event Effect Studies", D. Bisello, A. Candelori, P. Giubilato, A. Kaminski, D. Pantano, R. Rando, M. Tessaro and J. Wyss, Proceedings of the 7th European Conference on Radiation and Its Effects on Components and Systems (RADECS), 15-19 September 2003, ESA SP-536, pp.451-455.

PG3) "X-ray Radiation Source for Total Dose Radiation Studies", D. Bisello, A. Candelori, A. Kaminski, A. Litovchenko, E. Noah and L. Stefanutti, Radiation Physics and Chemistry, vol.71, 2004, pp.713-715.

PG4) "The SIRAD Irradiation Facility for Radiation Damage Studies Induced by High-Energy Ions", D. Bisello, A. Candelori, P. Giubilato, A. Kaminski, D. Pantano, R. Rando, M. Tessaro and J. Wyss, Radiation Physics and Chemistry, vol.71, 2004, pp.717-719.

PG5) "Radiation Hardness Qualification of the APV25 Chip Production for the CMS Experiment", A. Candelori, R. Bainbridge, P. Barillon, D. Bisello, M. J. French, G. Hall, A. Kaminski, V. Khomenkov, E. Noah, M. Raymond, L. Stefanutti and M. Tessaro, Proc. of the 2nd SIRAD Workshop, 1-2 April 2004, LNL-INFN (Rep) – 203/2004, ISBN 88-7337-007-1.

PG6) "Ion Electron Emission Microscopy at SIRAD", D. Bisello, A. Candelori, P. Giubilato, A. Kaminsky, S. Mattiazzo, M. Nigro, D. Pantano, R. Rando, M. Tessaro, J. Wyss, S. Bertazzoni, D. Di Giovenale, Nuclear Instruments and Methods in Physics Research, vol.B231, 2005, pp.65-69.

PG7) "Position Sensitive Detectors for Ion Electron Emission Microscopy", D. Bisello, A. Candelori, P. Giubilato, A. Kaminsky, S. Mattiazzo, M. Nigro, D. Pantano, R. Rando, M. Tessaro, J. Wyss, Nuclear Instruments and Methods in Physics Research, vol.A573, 2007, pp.23-26.

PG8) " Secondary Electron Yield of Au and Al₂O₃ Surfaces from Swift Heavy Ion Impact in the 2.5–7.9 MeV/amu Energy Range", D. Bisello, A. Candelori, P. Giubilato, A. Kaminsky, S. Mattiazzo, M. Nigro, D. Pantano, R. Rando, L. Silvestrin, M. Tessaro, J. Wyss, Nuclear Instruments and Methods in Physics Research, vol.B266, 2008, pp.173-180.

PG9) "Production Testing and Quality Assurance of CMS Silicon Microstrip Tracker Readout Chips", R. Bainbridge, P. Barrillon, G. Hall, J. Leaver, E. Noah, M. Raymond, D. Bisello, A. Candelori, A. Kaminsky, V. Khomenkov, L. Stefanutti, M. Tessaro, M. French, Nuclear Instruments and Methods in Physics Research, vol.A543, 2005, pp.619-644.

H) TESI DI DOTTORATO DI RICERCA

H1) Tesi di dottorato di ricerca in Ingegneria Elettronica e delle Telecomunicazioni: "Microstrip Detectors and Front-end Electronics: Performance, SPICE Simulations and Dielectric Reliability Issues ", Dottorando: A. Candelori, Coordinatore: Prof. Silvano Pupolin, Tutore: Prof. Alessandro Paccagnella, Università degli Studi di Padova, A.A. 1997-1998.